Thomas SchÃ¤pers

List of Publications by Year
in descending order

212 papers	4,449 citations	109311 35 h-index	144002 57 g-index
223 all docs	223 docs citations	223 times ranked	3476 citing authors

#	Article	IF	Citations
1	Experimental and theoretical approach to spin splitting in modulation-dopedInxGa1â^'xAs/InP quantum wells for Bâ†'0. Physical Review B, 1997, 55, R1958-R1961.	3.2	514
2	Effect of the heterointerface on the spin splitting in modulation doped InxGa1â^'xAs/InP quantum wells for Bâ†'0. Journal of Applied Physics, 1998, 83, 4324-4333.	2.5	283
3	Hall effect measurements on InAs nanowires. Applied Physics Letters, 2012, 101, 152106.	3.3	88
4	Realization of a vertical topological pâ€"n junction in epitaxial Sb2Te3/Bi2Te3 heterostructures. Nature Communications, 2015, 6, 8816.	12.8	85
5	Spin-orbit coupling and phase coherence in InAs nanowires. Physical Review B, 2010, 82, .	3.2	79
6	Signatures of interaction-induced helical gaps in nanowire quantum point contacts. Nature Physics, 2017, 13, 563-567.	16.7	77
7	Effect of Rashba spin-orbit coupling on magnetotransport inInGaAsâˆ•InPquantum wire structures. Physical Review B, 2004, 69, .	3.2	74
8	Molecular Beam Epitaxy Growth of GaAs/InAs Coreâ€"Shell Nanowires and Fabrication of InAs Nanotubes. Nano Letters, 2012, 12, 5559-5564.	9.1	71
9	Selective area growth and stencil lithography for in situ fabricated quantum devices. Nature Nanotechnology, 2019, 14, 825-831.	31.5	70
10	Flux Quantization Effects in InN Nanowires. Nano Letters, 2008, 8, 2834-2838.	9.1	69
11	Electronic Phase Coherence in InAs Nanowires. Nano Letters, 2011, 11, 3550-3556.	9.1	68
12	Suppression of weak antilocalization inGaxIn1â^'xAsâˆ•InPnarrow quantum wires. Physical Review B, 2006, 74, .	3.2	66
13	Effect of Si-doping on InAs nanowire transport and morphology. Journal of Applied Physics, 2011, 110, .	2.5	61
14	Superconductor/Semiconductor Junctions. Springer Tracts in Modern Physics, 2001, , .	0.1	60
15	Self-catalyzed VLS grown InAs nanowires with twinning superlattices. Nanotechnology, 2013, 24, 335601.	2.6	56
16	Field effect transistor based on single crystalline InSb nanowire. Journal of Materials Chemistry, 2011, 21, 2459.	6.7	54
17	Interference ferromagnet/semiconductor/ferromagnet spin field-effect transistor. Physical Review B, 2001, 64, .	3.2	53
18	Enhancement of spin injection from ferromagnetic metal into a two-dimensional electron gas using a tunnel barrier. Physical Review B, 2001, 64, .	3.2	52

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19	Weak antilocalization in a polarization-doped AlxGa1â^’xNâ^•GaN heterostructure with single subband occupation. Applied Physics Letters, 2006, 88, 022111.	3.3	52
20	Weak antilocalization in gate-controlledAlxGa1â^’xNâ^•GaNtwo-dimensional electron gases. Physical Review B, 2006, 73, .	3.2	51
21	Magnetosubbands of semiconductor quantum wires with Rashba spin-orbit coupling. Physical Review B, 2005, 71, .	3.2	50
22	Flux periodic magnetoconductance oscillations in GaAs/InAs core/shell nanowires. Physical Review B, 2014, 89, .	3.2	47
23	Electrical transport properties of single undoped and n-type doped InN nanowires. Nanotechnology, 2009, 20, 405206.	2.6	46
24	Ballistic Transport and Exchange Interaction in InAs Nanowire Quantum Point Contacts. Nano Letters, 2016, 16, 3116-3123.	9.1	46
25	Spin precession and modulation in ballistic cylindrical nanowires due to the Rashba effect. Physical Review B, 2011, 83, .	3.2	45
26	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 085603.	2.6	45
27	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. Journal of Applied Physics, 2012, 112, .	2.5	43
28	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. Nanotechnology, 2013, 24, 035203.	2.6	43
29	Quantum Transport and Nano Angle-resolved Photoemission Spectroscopy on the Topological Surface States of Single Sb2Te3 Nanowires. Scientific Reports, 2016, 6, 29493.	3.3	43
30	Demonstration of a current-controlled three-terminal Nbâ€“InxGa1â^’xAs/InP Josephson contact. Applied Physics Letters, 1998, 73, 2348-2350.	3.3	42
31	Growth, characterization, and transport properties of ternary (Bi_{1â^’<i>x</i>}Sb_{<i>x</i>})₂Te₃topological insulator layers. Journal of Physics Condensed Matter, 2016, 28, 495501.	1.8	41
32	Optimization of modulationâ€doped Ga1â^’xInxAs/InP heterostructures towards extremely high mobilities. Journal of Applied Physics, 1993, 73, 4489-4493.	2.5	40
33	Weak antilocalization in high mobility<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></ mathvariant="normal">As</mml:mi><mml:mo>â^•</mml:mo><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">P</mml:mi></mml:mrow></mml:ma	3.2	38
34	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (111) B using N2 carrier gas. Journal of Crystal Growth, 2009, 311, 3813-3816.	1.5	36
35	Electrical Spin Injection into InN Semiconductor Nanowires. Nano Letters, 2012, 12, 4437-4443.	9.1	36
36	Pâ€“N Junctions in Ultrathin Topological Insulator Sb₂Te₃/Bi₂Te₃ Heterostructures Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2016, 16, 2057-2061.	3.0	36

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37	Enhanced spin-orbit scattering length in narrow<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Al</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow> mathvariant="normal">N</mml:mi><mml:mo>â^•</mml:mo><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:m	3.2	34
38	Amphoteric Nature of Sn in CdS Nanowires. Nano Letters, 2014, 14, 518-523.	9.1	32
39	Selective area growth of Bi2Te3 and Sb2Te3 topological insulator thin films. Journal of Crystal Growth, 2016, 443, 38-42.	1.5	32
40	Electron interference in a T-shaped quantum transistor based on Schottky-gate technology. Physical Review B, 1996, 53, 9959-9963.	3.2	30
41	Rashba effect in InGaAsâ^•InP parallel quantum wires. Applied Physics Letters, 2006, 88, 032102.	3.3	30
42	Manipulating InAs nanowires with submicrometer precision. Review of Scientific Instruments, 2011, 82, 113705.	1.3	30
43	Controlled wurtzite inclusions in self-catalyzed zinc blende IIIâ€"V semiconductor nanowires. Journal of Crystal Growth, 2013, 378, 506-510.	1.5	30
44	Aharonov-Bohm effect in quasi-one-dimensionalIn0.77Ga0.23As/InP rings. Physical Review B, 1995, 51, 4336-4342.	3.2	29
45	Properties of lateral Nb contacts to a two-dimensional electron gas in anIn0.77Ga0.23As/InP heterostructure. Physical Review B, 1996, 54, 17018-17028.	3.2	29
46	Temperature dependence of the phase-coherence length in InN nanowires. Applied Physics Letters, 2008, 92, .	3.3	29
47	Josephson supercurrent in Nb/InN-nanowire/Nb junctions. Applied Physics Letters, 2010, 96, 132504.	3.3	29
48	Resolving ambiguities in nanowire field-effect transistor characterization. Nanoscale, 2015, 7, 18188-18197.	5.6	29
49	Josephson effect in Nb/two-dimensional electron gas structures using a pseudomorphic InxGa1â^’xAs/InP heterostructure. Applied Physics Letters, 1997, 71, 3575-3577.	3.3	28
50	Phase-coherent transport in InN nanowires of various sizes. Physical Review B, 2008, 77, .	3.2	27
51	Crystal Phase Selective Growth in GaAs/InAs Coreâ€"Shell Nanowires. Crystal Growth and Design, 2014, 14, 1167-1174.	3.0	27
52	High-frequency (THz) studies of quantum-effect devices. Semiconductor Science and Technology, 1996, 11, 1888-1894.	2.0	26
53	Andreev reflection and strongly enhanced magnetoresistance oscillations in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></ mathvariant="normal">As</mml:mi><mml:mo>â^•</mml:mo><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">P</mml:mi></. Physical Review B, 20	3.2	26
54	Crystal Phase Transformation in Self-Assembled InAs Nanowire Junctions on Patterned Si Substrates. Nano Letters, 2016, 16, 1933-1941.	9.1	26

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55	Spin-splitting analysis of a two-dimensional electron gas in almost strain-free<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mrow><mml:mn>0.89</mml: Physical Review B, 2008, 77, .	3.2	25
56	Measurement of effective electron mass in biaxial tensile strained silicon on insulator. Applied Physics Letters, 2009, 95, .	3.3	25
57	Effect of electronâ€electron interaction on hot ballistic electron beams. Applied Physics Letters, 1995, 66, 3603-3605.	3.3	24
58	Spin-orbit coupling and phase-coherent transport in InN nanowires. Physical Review B, 2009, 80, .	3.2	24
59	Crossover from Josephson Effect to Single Interface Andreev Reflection in Asymmetric Superconductor/Nanowire Junctions. Nano Letters, 2014, 14, 4977-4981.	9.1	24
60	Weak (anti)localization in tubular semiconductor nanowires with spin-orbit coupling. Physical Review B, 2016, 93, .	3.2	24
61	Adiabatic Edge Channel Transport in a Nanowire Quantum Point Contact Register. Nano Letters, 2016, 16, 4569-4575.	9.1	24
62	Electronic Transport with Dielectric Confinement in Degenerate InN Nanowires. Nano Letters, 2012, 12, 2768-2772.	9.1	23
63	Extremely high electron mobilities in modulation doped Ga1â^'xInxAs/InP heterostructures grown by LP-MOVPE. Journal of Crystal Growth, 1992, 116, 521-523.	1.5	22
64	MBE growth of Al/InAs and Nb/InAs superconducting hybrid nanowire structures. Nanoscale, 2017, 9, 16735-16741.	5.6	22
65	Quantum Transport in Topological Surface States of Selectively Grown Bi₂Te₃ Nanoribbons. Advanced Electronic Materials, 2020, 6, 2000205.	5.1	21
66	Local suppression of Josephson currents in niobium/two-dimensional electron gas/niobium structures by an injection current. Physical Review B, 1999, 59, 11197-11200.	3.2	20
67	Universal conductance fluctuations and localization effects in InN nanowires connected in parallel. Journal of Applied Physics, 2010, 108, .	2.5	20
68	Current-injection in a ballistic multiterminal superconductor/two-dimensional electron gas Josephson junction. Physical Review B, 2003, 67, .	3.2	19
69	Magnetic and structural properties of GaN thin layers implanted with Mn, Cr, or V ions. Journal of Applied Physics, 2004, 96, 5663-5667.	2.5	18
70	Magnetotransport signatures of three-dimensional topological insulator nanostructures. Physical Review B, 2018, 97, .	3.2	18
71	Photon-assisted transport through quantized energy states in a lateral dual-gate device. Physical Review B, 1995, 52, 14834-14838.	3.2	17
72	Splitting of the subgap resistance peak in superconductor/two-dimensional electron gas contacts at high magnetic fields. Physical Review B, 2000, 61, 12463-12466.	3.2	17

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73	Giant Magnetoconductance Oscillations in Hybrid Superconductorâˆ’Semiconductor Core/Shell Nanowire Devices. Nano Letters, 2014, 14, 6269-6274.	9.1	17
74	Micro-pixel light emitting diodes: Impact of the chip process on microscopic electro- and photoluminescence. Applied Physics Letters, 2015, 106, .	3.3	17
75	Electron-electron interaction in ballistic electron beams. Physical Review B, 1995, 51, 5099-5105.	3.2	16
76	Andreev reflection and enhanced subgap conductance in NbNâˆ•Auâˆ•InGaAsâ€InP junctions. Journal of Applied Physics, 2004, 96, 3366-3370.	2.5	16
77	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. Applied Physics Letters, 2012, 100, .	3.3	16
78	Demonstration of the N2 carrier process for LP-MOVPE of. Journal of Crystal Growth, 1997, 170, 103-108.	1.5	15
79	Optical and electrical properties of gold nanowires synthesized by electrochemical deposition. Journal of Applied Physics, 2011, 110, 094301.	2.5	15
80	Phase coherent transport in InSb nanowires. Applied Physics Letters, 2012, 101, 082103.	3.3	15
81	Zeeman splitting in ballistic GaInAsâˆ•InP split-gate quantum point contacts. Applied Physics Letters, 2007, 90, 122107.	3.3	14
82	Phase-coherence and symmetry in four-terminal magnetotransport measurements on InN nanowires. Applied Physics Letters, 2009, 94, 252107.	3.3	14
83	Reappearance of first Shapiro step in narrow topological Josephson junctions. Science Advances, 2021, 7, .	10.3	14
84	Quantized conductance in a split-gate point contact based on a pseudomorphic InGaAs/InP heterostructure. Journal of Applied Physics, 1996, 79, 871.	2.5	13
85	Control of Aharonovâ€“Bohm oscillations in a AlGaAs/GaAs ring by asymmetric and symmetric gate biasing. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 9, 635-641.	2.7	13
86	Rashba effect in strained InGaAs/InP quantum wire structures. Science and Technology of Advanced Materials, 2003, 4, 19-25.	6.1	13
87	Coherent â€œMetallicâ€• Resistance and Medium Localization in a Disordered One-Dimensional Insulator. Physical Review Letters, 2003, 91, 136803.	7.8	13
88	Principles of electrochemical nanotechnology and their application for materials and systems. Electrochimica Acta, 2005, 51, 775-786.	5.2	13
89	Epitaxial growth of Fe on GaN(0001): structural and magnetic properties. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 754-757.	1.8	13
90	Spinâ€“orbit coupling in Ga_{<i>x</i>}In_{1âˆ’<i>x</i>}As/InP two-dimensional electron gases and quantum wire structures. Semiconductor Science and Technology, 2009, 24, 064001.	2.0	13

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91	Influence of barrier thickness on AlInN/AlN/GaN heterostructures and device properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1041.	0.8	13
92	Magnetoresistance oscillations in MBE-grown Sb2Te3 thin films. Applied Physics Letters, 2017, 110, .	3.3	13
93	Stencil lithography of superconducting contacts on MBE-grown topological insulator thin films. Journal of Crystal Growth, 2017, 477, 183-187.	1.5	13
94	Experimental determination of Rashba and Dresselhaus parameters and<i>g</i>[*]-factor anisotropy via Shubnikov-de Haas oscillations. New Journal of Physics, 2017, 19, 103012.	2.9	13
95	Properties of the twoâ€dimensional electron gas in modulationâ€doped GaInAs(P)/InP structures grown by lowâ€pressure metalorganic vaporâ€phase epitaxy. Journal of Applied Physics, 1989, 66, 697-703.	2.5	12
96	Magnetotransport and photoluminescence of two-dimensional hole gases in Si/Si1â^'xGex/Si heterostructures. Physical Review B, 1994, 50, 18113-18123.	3.2	12
97	Phase-coherent loops in selectively-grown topological insulator nanoribbons. Nanotechnology, 2020, 31, 325001.	2.6	12
98	Weak antilocalization measurements on a 2-dimensional electron gas in an InGaSb/InAlSb heterostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4227-4230.	0.8	11
99	Origin and limiting mechanism of induced nonequilibrium currents in gated two-dimensional electron systems. Physical Review B, 2009, 80, .	3.2	11
100	Two-Dimensional Optical Control of Electron Spin Orientation by Linearly Polarized Light in InGaAs. Physical Review Letters, 2010, 105, 246603.	7.8	11
101	Fully <i>in situ</i> Nb/InAs-nanowire Josephson junctions by selective-area growth and shadow evaporation. Nanoscale Advances, 2021, 3, 1413-1421.	4.6	11
102	Investigation of Ferromagnetic Microstructures by Local Hall Effect and Magnetic Force Microscopy. Japanese Journal of Applied Physics, 2002, 41, 2497-2500.	1.5	10
103	Localized electrochemical oxidation of thin Nb Films in microscopic and nanoscopic dimensions. Surface Science, 2005, 597, 173-180.	1.9	10
104	Rashba effect in GaxIn1-xAs/InP quantum wire structures. Applied Physics A: Materials Science and Processing, 2007, 87, 577-584.	2.3	10
105	Low-temperature conductance of the weak junction in InAs nanowire in the field of AFM scanning gate. JETP Letters, 2011, 93, 10-14.	1.4	10
106	Frequency anomaly in the Rashba-effect induced magnetization oscillations of a high-mobility two-dimensional electron system. Physical Review B, 2013, 87, .	3.2	10
107	Electronic Properties of Complex Selfâ€Assembled InAs Nanowire Networks. Advanced Electronic Materials, 2016, 2, 1500460.	5.1	10
108	Angle-dependent magnetotransport in GaAs/InAs core/shell nanowires. Scientific Reports, 2016, 6, 24573.	3.3	10

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109	Electron Interference in Hall Effect Measurements on GaAs/InAs Core/Shell Nanowires. Nano Letters, 2017, 17, 128-135.	9.1	10
110	Magnetoconductance correction in zinc-blende semiconductor nanowires with spin-orbit coupling. Physical Review B, 2017, 96, .	3.2	10
111	Strain relaxation and ambipolar electrical transport in GaAs/InSb coreâ€“shell nanowires. Nanoscale, 2017, 9, 18392-18401.	5.6	10
112	Adjustment of the critical current in a Nbâ€“InxGa1â^'xAs/InP Josephson contact by light exposure. Applied Physics Letters, 1999, 75, 391-393.	3.3	9
113	On the choice of precursors for the MOVPE-growth of high-quality Al0.30Ga0.70As/GaAs v-groove quantum wires with large subband spacing. Journal of Crystal Growth, 2000, 221, 91-97.	1.5	9
114	Electron transport in modulation-doped GaAs v-groove quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 760-765.	2.7	9
115	Influence of growth temperature on GaN:Cr incorporation and structural properties in MOVPE. Journal of Crystal Growth, 2009, 312, 1-9.	1.5	9
116	Electrical and structural studies of AlGaAs/GaAs wires grown on patterned substrates. Applied Surface Science, 1998, 123-124, 687-693.	6.1	8
117	Electron states, magneto-transport and carrier dynamics in modulation-dopedV-groove quantum wires. Solid-State Electronics, 1998, 42, 1245-1249.	1.4	8
118	Hybrid superconductor/semiconductor step junctions with three terminals. Journal of Applied Physics, 1998, 83, 8077-8079.	2.5	8
119	Comparison of InAs nanowire conductivity: influence of growth method and structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 230-234.	0.8	8
120	The electronic transport of top subband and disordered sea in an InAs nanowire in the presence of a mobile gate. Journal of Physics Condensed Matter, 2014, 26, 165304.	1.8	8
121	Simultaneous Integration of Different Nanowires on Single Textured Si (100) Substrates. Nano Letters, 2015, 15, 1979-1986.	9.1	8
122	Electrical properties of lightly Ga-doped ZnO nanowires. Semiconductor Science and Technology, 2017, 32, 125010.	2.0	8
123	Exploiting topological matter for Majorana physics and devices. Solid-State Electronics, 2019, 155, 99-104.	1.4	8
124	Gate-induced decoupling of surface and bulk state properties in selectively-deposited Bi$_2$Te$_3$ nanoribbons. SciPost Physics Core, 2022, 5, .	2.8	8
125	Carrier relaxation inGaAsv-groove quantum wires and the effects of localization. Physical Review B, 2004, 70, .	3.2	7
126	Suppression of weak antilocalization in anAlxGa1â^'xNâ•GaNtwo-dimensional electron gas by an in-plane magnetic field. Physical Review B, 2007, 75, .	3.2	7

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127	Investigation of the surface properties of gold nanowire arrays. Applied Surface Science, 2011, 258, 147-150.	6.1	7
128	Investigations of local electronic transport in InAs nanowires by scanning gate microscopy at liquid helium temperatures. JETP Letters, 2014, 100, 32-38.	1.4	7
129	Quantum dots in InAs nanowires induced by surface potential fluctuations. Nanotechnology, 2014, 25, 135203.	2.6	7
130	Dresselhaus spin-orbit coupling in [111]-oriented semiconductor nanowires. Physical Review B, 2019, 99, .	3.2	7
131	Observation of quantized conductance in split-gate In0.53Ga0.47As/In0.77Ga0.23As/InP point contacts using Cr/Au p-InP Schottky barriers. Journal of Applied Physics, 1998, 83, 2360-2362.	2.5	6
132	Suppression of Josephson currents in ballistic junctions by an injection current. Superlattices and Microstructures, 1999, 25, 1033-1040.	3.1	6
133	Coherent resistance of a disordered one-dimensional wire:â€‚â€‚Expressions for all moments and evidence for non-Gaussian distribution. Physical Review B, 2003, 67, .	3.2	6
134	Rashba effect in gated InGaAs/InP quantum wire structures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 933-936.	2.7	6
135	Shot noise of large charge quanta in superconductor/semiconductor/superconductor junctions. Physical Review B, 2005, 71, .	3.2	6
136	Study on growth and electrical performance of doubleâ€heterostructure AlGaN/GaN/AlGaN fieldâ€effectâ€transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1003.	0.8	6
137	Distortions of the coulomb blockade conductance line in scanning gate measurements of inas nanowire based quantum dots. Journal of Experimental and Theoretical Physics, 2013, 116, 138-144.	0.9	6
138	Phase coherent transport in hollow InAs nanowires. Applied Physics Letters, 2014, 105, 113111.	3.3	6
139	Impact of Tunnel-Barrier Strength on Magnetoresistance in Carbon Nanotubes. Physical Review Applied, 2016, 5, .	3.8	6
140	Phase-coherent transport in selectively grown topological insulator nanodots. Nanotechnology, 2019, 30, 055201.	2.6	6
141	Flux periodic oscillations and phase-coherent transport in GeTe nanowire-based devices. Nature Communications, 2021, 12, 754.	12.8	6
142	Optical measurements of carrier relaxation and transport in single GaAs v-groove quantum wire structures. Physica B: Condensed Matter, 2002, 314, 413-416.	2.7	5
143	Strain-enhanced electron mobility anisotropy in InxGa1âxAs/InP two-dimensional electron gases. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1130-1133.	2.7	5
144	Quantum transport in narrowâ€gap semiconductor nanocolumns. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 386-389.	0.8	5

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145	LaLuO₃as a high-<i>k</i>gate dielectric for InAs nanowire structures. Semiconductor Science and Technology, 2010, 25, 085001.	2.0	5
146	New method of creation of a rearrangeable local Coulomb potential profile and its application for investigations of local conductivity of InAs nanowires. Physica E: Low-Dimensional Systems and Nanostructures, 2011, 44, 690-695.	2.7	5
147	Scanning tunneling microscopy with InAs nanowire tips. Applied Physics Letters, 2012, 101, .	3.3	5
148	Monitoring structural influences on quantum transport in InAs nanowires. Applied Physics Letters, 2012, 101, 062104.	3.3	5
149	Direct observation of standing electron waves in diffusively conducting inas nanowire. JETP Letters, 2012, 96, 109-112.	1.4	5
150	Proximityâ€Effectâ€Induced Superconductivity in Nb/Sb 2 Te 3 â€Nanoribbon/Nb Junctions. Annalen Der Physik, 2020, 532, 2000273.	2.4	5
151	Phase coherent transport and spin-orbit interaction in GaAs/InSb core/shell nanowires. Semiconductor Science and Technology, 2020, 35, 085003.	2.0	5
152	In-plane magnetic field-driven symmetry breaking in topological insulator-based three-terminal junctions. Communications Materials, 2021, 2, .	6.9	5
153	Photoluminescence and magnetotransport of 2-D hole gases in Si/SiGe/Si heterostructures. Solid-State Electronics, 1994, 37, 957-959.	1.4	4
154	Optical and transport studies of hot electrons in modulation-doped quantum wires. Physica B: Condensed Matter, 1999, 272, 101-106.	2.7	4
155	Multiple Andreev reflections in ballistic Nb-InGaAs/InP-Nb junctions. Superlattices and Microstructures, 1999, 25, 851-859.	3.1	4
156	Preparation of transparent Nb/two-dimensional electron gas contacts by using electron cyclotron resonance plasma cleaning. Journal of Applied Physics, 2000, 88, 4440.	2.5	4
157	Model for ballistic spin-transport in ferromagnet/two-dimensional electron gas/ferromagnet structures. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 564-567.	2.7	4
158	The growth of Cr-doped GaN by MOVPE towards spintronic applications. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 72-77.	1.8	4
159	Negative differential conductance in InAs wire based double quantum dot induced by a charged AFM tip. Journal of Experimental and Theoretical Physics, 2012, 115, 1062-1067.	0.9	4
160	Gate-induced transition between metal-type and thermally activated transport in self-catalyzed MBE-grown InAs nanowires. Nanotechnology, 2013, 24, 325201.	2.6	4
161	Correlations of the mutual positions of the nodes of charge density waves in side-by-side placed InAs wires measured with scanning gate microscopy. JETP Letters, 2015, 101, 628-632.	1.4	4
162	Quantum interferometer based on GaAs/InAs core/shell nanowires connected to superconducting contacts. Semiconductor Science and Technology, 2018, 33, 064001.	2.0	4

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